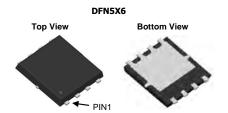


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N-Channel 100 V (D-S) MOSFET

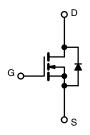
PRODUCT SUMMARY						
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A) ^{a, d}	Q _g (Typ.)			
100	0.0065 at V _{GS} = 10 V	110	128nC			

FEATURES • TrenchFET IIPower MOSFET COMPLIANT • 100 % Rgand UIS Tested



APPLICATIONS

- Synchronous rectification
- Primary side switch
- DC/DC converters
- OR-ing
- Power supplies
- Motor drive control
- Battery and load switch



N-Channel MOSFET

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V_{DS}	100	V
Gate-source voltage		V_{GS}	± 20	V
	T _C = 25 °C		110 ^a	
Continuous dusin suggest (T 150 °C)	T _C = 70 °C	1.	89.8	
Continuous drain current (T _J = 150 °C)	T _A = 25 °C	I _D	41.2 b, c	
	T _A = 70 °C	1	27.4 ^{b, c}	^
Pulsed drain current (t = 100 µs)		I _{DM}	440	A
Continuous source-drain diode current	T _C = 25 °C		110 a	
	T _A = 25 °C		6.6 b, c	
Single pulse avalanche current	L = 0.1 mH	I _{AS}	68	
Single pulse avalanche energy		E _{AS}	113	mJ
	T _C = 25 °C		175	
Maniana a succession attack	T _C = 70 °C		110	14/
Maximum power dissipation	T _A = 25 °C	P _D	7.25 ^{b, c}	- W
	T _A = 70 °C	1	5 b, c	
Operating junction and storage temperature range		T _J , T _{stq}	-55 to +150	°C
Soldering recommendations (peak temperature) c			260	- °C

THERMAL RESISTANCE RATINGS								
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT			
Maximum junction-to-ambient ^b	t ≤ 10 s	R_{thJA}	12	20				
Maximum junction-to-case (drain)	Steady state	R_{thJC}	0.7	1	°C/W			
Maximum junction-to-case (source)	Steady state	R _{th.IC}	1.0	1.4				

- a. Based on T_C = 25 °C.
 b. Surface mounted on 1" x 1" FR4 board.
- d. Calculated based on maximum junction temperature.

PARAMETER SYMBOL		TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static				•	•	
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	100	-	-	V
V _{DS} temperature coefficient	$\Delta V_{DS}/T_{J}$	I _D = 250 μA		56	-	mV/°C
V _{GS(th)} temperature coefficient	$\Delta V_{GS(th)}/T_J$	I _D = 250 μA	-	-6	-	IIIV/ C
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2	-	4	V
Gate-source leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	100	nA
Zero gate voltage drain current	I _{DSS}	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	1	μΑ
	.033	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 70 \text{ °C}$	-	-	10	
On-state drain current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	110	-	-	Α
Drain-source on-state resistance a	R _{DS(on)}	$V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$	-	0.0065	0.0080	Ω
Forward transconductance ^a	9 _{fs}	$V_{DS} = 10 \text{ V}, I_{D} = 20 \text{ A}$	ı	68	-	S
Dynamic ^b						
Input capacitance	C _{iss}		=.	6285	=.	pF
Output capacitance	C _{oss}	$V_{DS} = 50 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	=.	1819	-	
Reverse transfer capacitance	C _{rss}		-	206	-	
Total gate charge	Qg		-	128	-	nC
Gate-source charge	Q _{gs}	$V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 20 \text{ A}$	-	10	-	
Gate-drain charge	Q _{gd}		-	10.6	-	
Output charge	Q _{oss}	$V_{DS} = 50 \text{ V}, V_{GS} = 0 \text{ V}$	-	69	104	
Gate resistance	R_g	f = 1 MHz	0.3	1	2	Ω
Turn-on delay time	t _{d(on)}		-	13	26	ns
Rise time	t _r	$V_{DD} = 50 \text{ V}, R_L = 2.5 \Omega, I_D \cong 20 \text{ A},$	-	14	28	
Turn-off delay time	t _{d(off)}	$V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	35	70	
Fall time	t _f		-	9	18	
Drain-Source Body Diode Characteristics						
Continuous source-drain diode current	I _S	T _C = 25 °C	-	-	110	^
Pulse diode forward current (t _p = 100 μs)	I _{SM}		-	-	440	A
Body diode voltage	V _{SD}	I _S = 5 A, V _{GS} = 0 V	-	0.7	1.2	V
Body diode reverse recovery time	t _{rr}		-	54	100	ns
Body diode reverse recovery charge	Q _{rr}	1 00 A di/d+ 100 A/va T 05 °C	-	76	140	nC
Reverse recovery fall time	ta	$I_F = 20 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 ^{\circ}\text{C}$	-	27	-	
Reverse recovery rise time	t _b	7		27	-	ns

Notes

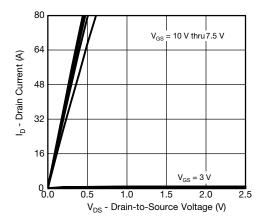
a.P ulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

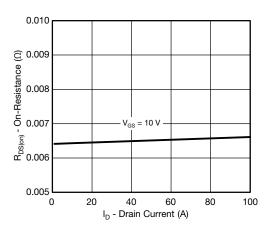
b. Guaranteed by design, not subject to production testing



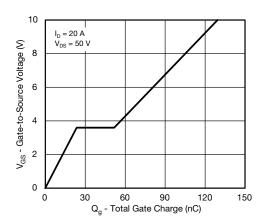
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



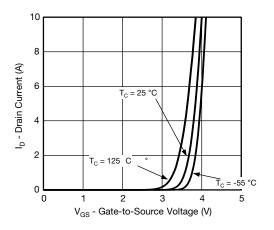
Output Characteristics



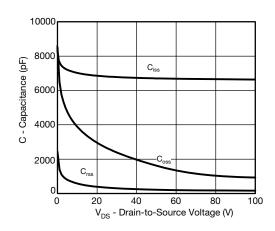
On-Resistance vs. Drain Current and Gate Voltage



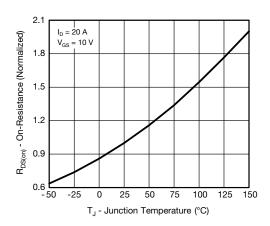
Gate Charge



Transfer Characteristics



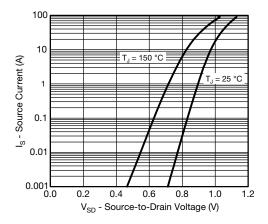
Capacitance



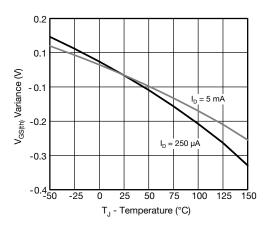
On-Resistance vs. Junction Temperature



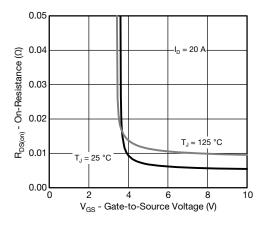
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



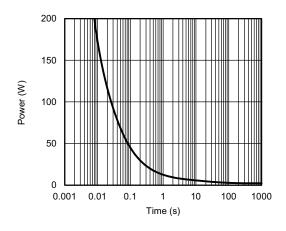
Source-Drain Diode Forward Voltage



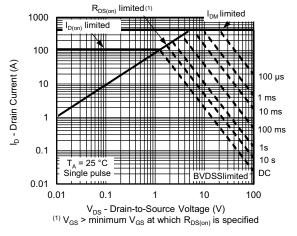
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



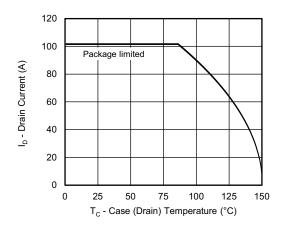
Single Pulse Power, Junction-to-Ambient



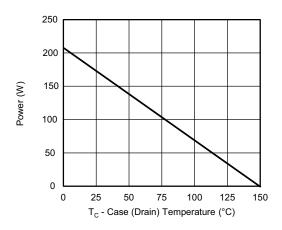
Safe Operating Area, Junction-to-Ambient



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



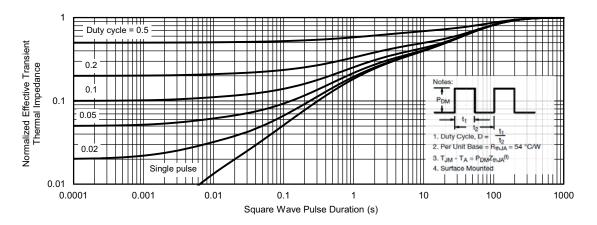
Current Derating a



Power, Junction-to-Case

Note

a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



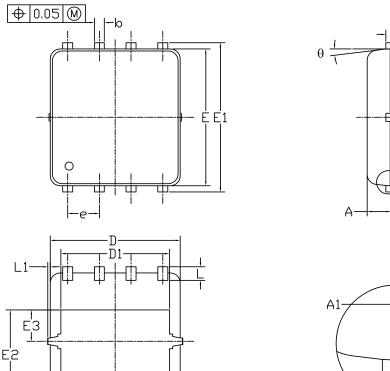
Normalized Thermal Transient Impedance, Junction-to-Ambient

VIEW 'A'



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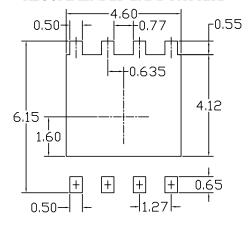
DFN5x6_8L_EP1_P PACKAGE OUTLIN



A1

<u>VIEW 'A'</u> (SCALE 5:1)

RECOMMENDED LAND PATTERN



SYMBOLS DIMENSIONS IN MILLIMETERS		DIMENSIONS IN INCHES				
3 I MBOLS	MIN	NOM	MAX	MIN	NOM	MAX
A	0.85	0. 95	1.00	0.033	0.037	0.039
Al	0.00		0.05	0.000		0.002
b	0.30	0.40	0.50	0.012	0.016	0.020
c	0. 15	0. 20	0. 25	0.006	0.008	0.010
D	4. 80	5. 20	5. 30	0. 201	0. 205	0. 209
D1	4. 25	4. 35	4. 45	0. 167	0.171	0. 175
Е	5. 45	5. 55	5. 65	0. 215	0. 219	0. 222
E1	5. 95	6.05	6. 15	0. 234	0. 238	0. 242
E2	3. 525	3.625	3. 725	0. 139	0. 143	0. 147
E3	1. 175	1. 275	1. 375	0.046	0.050	0.054
e	1. 27 BSC			0.050 BSC		
L	0.45	0. 55	0.65	0.018	0.022	0.026
L1	0		0. 15	0		0.006
L2	0.68 REF			0.027 REF		
θ	0°		10°	0°		10°

NOTE

- 1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS. MOLD FLASH AT THE NON-LEAD SIDES SHOULD BE LESS THAN 6 MILS EACH.
- 2. CONTROLLING DIMENSION IS MILLIMETER. CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.

UNIT: mm

BOTTOM VIEW





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